

IN THE CLAIMS:

Please cancel claims 2-3 without prejudice, and amend claims 1, 4 and 6 as follows:

1. (Currently Amended) An exposure mask for use in step exposure of a pattern to be formed on a TFT substrate, the exposure mask having pattern-forming portions each formed with a pattern portion for one pixel and shield portions each for blocking transmission of exposure light for one pixel,

wherein in ~~ana~~ a joint area corresponding to an overlapping exposure area in the step exposure, ~~a plurality of the pattern-forming portions and a plurality of the shield portions are mosaically arranged, such that areas between one shield portions and other shield portions vertically or laterally adjacent to the one shield portions are shielded~~ a first end portion is formed in which a plurality of the pattern-forming portions and a plurality of the shield portions, each formed with a pattern portion for one pixel, are mosaically arranged with an area proportion changing along with the joint area, and a second end portion is formed opposite and complementary to the first end portion in which the area proportion changes along with the joint area,

the shield portions including between the pattern-forming portions first shield portions smaller than the pattern-forming portions and second shield portions adjacent to each other and equal in size to the pattern-forming portions.

2-3. (Cancelled)

4. (Currently Amended) The exposure mask according to claim 1, wherein the pattern-forming portions and the shield portions are arranged ~~mosaically~~mosaically, in respective units of two or more adjacent pattern-forming portions and two or more adjacent shield portions identical in number to a number of pattern-forming portions of one unit.

5. (Original) The exposure mask according to claim 1, wherein the shield portions are arranged such that the shield portions are progressively reduced in number toward a center of the exposure mask.

6. (Currently Amended) A pattern exposure method by way of exposing a pattern to be formed on a TFT substrate by ~~step exposure~~step exposure using an exposure mask ~~having pattern-forming portions each formed with a pattern portion for one pixel and a plurality of shield portions each for blocking transmission of exposure light for one pixel~~a plurality of times, the method comprising:

a first exposure step of exposing a first pattern using a mask ~~pattern in which a plurality of the pattern-forming portions and a plurality of the shield portions are mosaically arranged at opposite end portions thereof, such that areas between one shield portions and~~

~~other shield portions vertically or laterally adjacent to the one shield portions are shielded;~~
and,

a second exposure step of exposing a second pattern using the exposure mask,
such that an end of the second pattern to be formed is adjacent to the first pattern and an end
of the first pattern overlap each other,

the exposure mask including pattern-forming portions each formed with a
pattern portion for one pixel and a plurality of shield portions each for blocking transmission
of exposure light for one pixel,

wherein in a joint area corresponding to an overlapping exposure area in the
step exposure, a first end portion is formed in which a plurality of the pattern-forming
portions and a plurality of the shield portions, each formed with a pattern portion for one
pixel, are mosaically arranged with an area proportion changing along with the joint area, and
a second end portion is formed opposite and complementary to the first end portion in which
the area proportion changes along with the joint area,

the shield portions including between the pattern-forming portions first shield
portions that are smaller than the pattern-forming portions and second shield portions that are
adjacent to each other and equal in size to the pattern-forming portions.